

Appl. No. : **10/804,584**
Filed : **March 16, 2004**

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0001] with the following amended paragraph:

This application is a continuation of U.S. Patent Application No. 10/068,465, filed February 6, 2002 (now U.S. Patent No. 6,735,112).

Please replace the abstract with the following amended abstract:

A magneto-resistive memory comprises~~es~~**[[ing]]** magneto-resistive memory cells ~~is disclosed,~~ comprising two pinned magnetic layers on one side of a free magnetic layer. The pinned magnetic layers are formed with anti-parallel magnetization orientations such that a net magnetic moment of the two layers is substantially zero. The influence of pinned magnetic layers on free magnetic layer magnetization orientations is substantially eliminated, allowing for increased predictability in switching behavior and increased write selectivity of memory cells.